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PATENT

ABSTRACT

5 A semiconductor chip is ESD protected, in part,
by utilizing floating lateral clamp diodes. Unlike
conventional clamp diodes, which are based upon
parasitic bipolar devices associated with large MOS
transistors, the floating lateral clamp diodes
utilize a well formed in the substrate as the
cathode, and a plurality of regions of the opposite
10 conductivity type which are formed in the well as the
anode.